

isc N-Channel MOSFET Transistor

2SK1409

DESCRIPTION

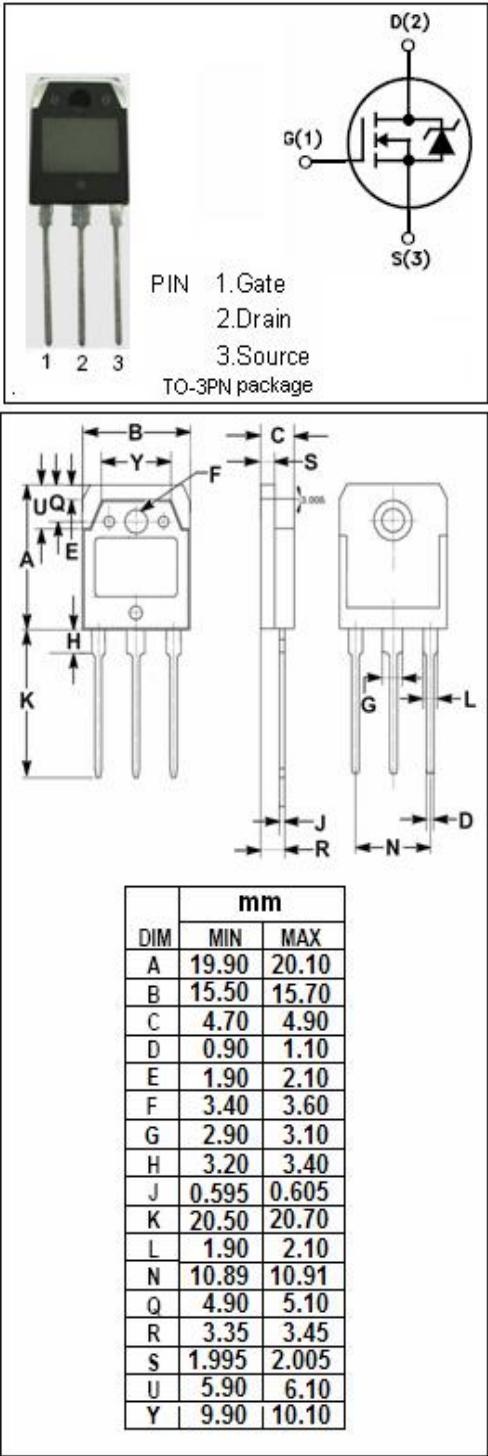
- Drain Current  $-I_D=20A @ T_C=25^{\circ}C$
- Drain Source Voltage-  
:  $V_{DSS}=450$  (Min)

APPLICATIONS

- Designed especially for high voltage,high speed applications, such as off-line switching power supplies , UPS,AC and DC motor controls,relay and solenoid drivers.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	ARAMETER	VALUE	UNI T
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	450	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $TC=25^{\circ}C$	20	A
$P_{tot}$	Total Dissipation@ $TC=25^{\circ}C$	250	W
$T_j$	Max. Operating Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-55~150	$^{\circ}C$



**isc N-Channel Mosfet Transistor****2SK1409****• ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0; I <sub>D</sub> = 10mA	450			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = 0V; I <sub>D</sub> =1mA	2.0	3.0	4.0	V
R <sub>DS(on)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =10A			0.25	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0			± 100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =450V; V <sub>GS</sub> = 0			500	uA